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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	F ² MC-16FX
Core Size	16-Bit
Speed	56MHz
Connectivity	CANbus, EBI/EMI, I ² C, LINbus, SCI, UART/USART
Peripherals	DMA, LVD, LVR, POR, PWM, WDT
Number of I/O	51
Program Memory Size	160KB (160K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 15x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/mb96f355rsbpmc1-gse2

■ PRODUCT LINEUP

Features		MB96V300B	MB96(F)35x				
Produc	ct type	Evaluation sample	Flash product: MB96F35x Mask ROM product: MB9635x				
Product options							
Υ	S		Low voltage reset persistently on / Single clock devices				
R	S		Low voltage reset can be disabled / Single clock devices				
Υ\	W	1	Low voltage reset persistently on / Dual clock devices				
R\	W	NA NA	Low voltage reset can be disabled / Dual clock devices				
А	S		No CAN / Low voltage reset can be disabled / Single clock devices				
Al	W		No CAN / Low voltage reset can be disabled / Dual clock devices				
Flash/ ROM	RAM						
96KB	8KB	ROM/Flash	MB96F353R, MB96F353A				
160KB	8KB	memory emulation by external RAM,	MB96F355R, MB96F355A				
288KB	12KB	92KB internal RAM	MB96F356Y, MB96F356R, MB96F356A				
Pack	kage	BGA416	FPT-64P-M23/24				
DΝ	ЛΑ	16 channels	4 channels				
USA	ART	10 channels	4 channels				
12	С	2 channels	1 channel				
A/D Co	nverter	40 channels	15 channels				
A/D Converte Voltage		yes	No				
16-bit Rel	oad Timer	6 channels + 1 channel (for PPG)	4 channels + 1 channel (for PPG)				
16-bit Free Tin	•	4 channels	4 channels (2 channels with external clock input pin)				
16-bit Outpu	ut Compare	12 channels	4 channels				
16-bit Inpu	ut Capture	12 channels	6 channels (plus 2 channels for LIN USART)				
16-bit Prog Pulse G		20 channels	20 channels				
CAN In	terface	5 channels	MB96F35xA: no MB96F353R/F355R: 1 channel MB96F356Y/R: 2 channels				
External I	Interrupts	16 channels	13 channels				
Non-Maskal	ble Interrupt		1 channel				

Features	MB96V300B	MB96(F)35x			
Real Time Clock		1			
I/O Ports	136 49 for part number with suffix "W", 51 for part number with suffix				
External bus interface	Yes				
Chip select		6 signals			
Clock output function		2 channels			
Low voltage reset	Yes				
On-chip RC-oscillator	Yes				

■ PIN CIRCUIT TYPE

Pin circuit types

FPT-64P-M23/24						
Pin no.	Circuit type *1					
1	Supply					
2	G					
3 to 15	I					
16,17	Н					
18	Supply					
19,20	B*2					
19,20	H _{*3}					
21 to 23	С					
24 to 44	Н					
45	E					
46,47	Α					
48,49	Supply					
50	F					
51	Н					
52,53	N					
54 to 61	Н					
62,63	I					
64	Supply					

^{*1:} Please refer to "■ I/O CIRCUIT TYPE" for details on the I/O circuit types

^{*2:} Devices with suffix "W"

^{*3:} Devices without suffix "W"

I/O map MB96(F)35x (5 of 28)

Address	Register	Abbreviation 8-bit access	Abbreviation 16-bit access	Access
000083н	PPG1 - Period setting register			W
000084н	PPG1 - Duty cycle register		PDUT1	W
000085н	PPG1 - Duty cycle register			W
000086н	PPG1 - Control status register Low	PCNL1	PCN1	R/W
000087н	PPG1 - Control status register High	PCNH1		R/W
000088н	PPG2 - Timer register		PTMR2	R
000089н	PPG2 - Timer register			R
00008Ан	PPG2 - Period setting register		PCSR2	W
00008Вн	PPG2 - Period setting register			W
00008Сн	PPG2 - Duty cycle register		PDUT2	W
00008Dн	PPG2 - Duty cycle register			W
00008Ен	PPG2 - Control status register Low	PCNL2	PCN2	R/W
00008Fн	PPG2 - Control status register High	PCNH2		R/W
000090н	PPG3 - Timer register		PTMR3	R
000091н	PPG3 - Timer register			R
000092н	PPG3 - Period setting register		PCSR3	W
000093н	PPG3 - Period setting register			W
000094н	PPG3 - Duty cycle register		PDUT3	W
000095н	PPG3 - Duty cycle register			W
000096н	PPG3 - Control status register Low	PCNL3	PCN3	R/W
000097н	PPG3 - Control status register High	PCNH3		R/W
000098н	PPG7-PPG4 - General Control register 1 Low	GCN1L1	GCN11	R/W
000099н	PPG7-PPG4 - General Control register 1 High	GCN1H1		R/W
00009Ан	PPG7-PPG4 - General Control register 2 Low	GCN2L1	GCN21	R/W
00009Вн	PPG7-PPG4 - General Control register 2 High	GCN2H1		R/W
00009Сн	PPG4 - Timer register		PTMR4	R
00009Dн	PPG4 - Timer register			R
00009Ен	PPG4 - Period setting register		PCSR4	W
00009Fн	PPG4 - Period setting register			W
0000А0н	PPG4 - Duty cycle register		PDUT4	W

I/O map MB96(F)35x (8 of 28)

Address	Register	Abbreviation 8-bit access	Abbreviation 16-bit access	Access
00010Dн	DMA1 - I/O register address pointer high byte	IOAH1		R/W
00010Ен	DMA1 - Data counter low byte	DCTL1	DCT1	R/W
00010Fн	DMA1 - Data counter high byte	DCTH1		R/W
000110н	DMA2 - Buffer address pointer low byte	BAPL2		R/W
000111н	DMA2 - Buffer address pointer middle byte	BAPM2		R/W
000112н	DMA2 - Buffer address pointer high byte	BAPH2		R/W
000113н	DMA2 - DMA control register	DMACS2		R/W
000114н	DMA2 - I/O register address pointer low byte	IOAL2	IOA2	R/W
000115н	DMA2 - I/O register address pointer high byte	IOAH2		R/W
000116н	DMA2 - Data counter low byte	DCTL2	DCT2	R/W
000117н	DMA2 - Data counter high byte	DCTH2		R/W
000118н	DMA3 - Buffer address pointer low byte	BAPL3		R/W
000119н	DMA3 - Buffer address pointer middle byte	BAPM3		R/W
00011Ан	DMA3 - Buffer address pointer high byte	ВАРН3		R/W
00011Вн	DMA3 - DMA control register	DMACS3		R/W
00011Сн	DMA3 - I/O register address pointer low byte	IOAL3	IOA3	R/W
00011Dн	DMA3 - I/O register address pointer high byte	IOAH3		R/W
00011Ен	DMA3 - Data counter low byte	DCTL3	DCT3	R/W
00011Fн	DMA3 - Data counter high byte	DCTH3		R/W
000120н- 00017Fн	Reserved			-
000180н- 00037Fн	CPU - General Purpose registers (RAM access)	GPR_RAM		R/W
000380н	DMA0 - Interrupt select	DISEL0		R/W
000381н	DMA1 - Interrupt select	DISEL1		R/W
000382н	DMA2 - Interrupt select	DISEL2		R/W
000383н	DMA3 - Interrupt select	DISEL3		R/W
000384н- 00038Fн	Reserved			-
000390н	DMA - Status register low byte	DSRL	DSR	R/W
000391н	DMA - Status register high byte	DSRH		R/W

I/O map MB96(F)35x (10 of 28)

Address	Register	Abbreviation 8-bit access	Abbreviation 16-bit access	Access
0003ВDн	Memory Patch function - Patch address 1 high	PFAH1		R/W
0003ВЕн	Memory Patch function - Patch address 2 low	PFAL2		R/W
0003ВFн	Memory Patch function - Patch address 2 middle	PFAM2		R/W
0003С0н	Memory Patch function - Patch address 2 high	PFAH2		R/W
0003С1н	Memory Patch function - Patch address 3 low	PFAL3		R/W
0003С2н	Memory Patch function - Patch address 3 middle	PFAM3		R/W
0003С3н	Memory Patch function - Patch address 3 high	PFAH3		R/W
0003С4н	Memory Patch function - Patch address 4 low	PFAL4		R/W
0003С5н	Memory Patch function - Patch address 4 middle	PFAM4		R/W
0003С6н	Memory Patch function - Patch address 4 high	PFAH4		R/W
0003С7н	Memory Patch function - Patch address 5 low	PFAL5		R/W
0003С8н	Memory Patch function - Patch address 5 middle	PFAM5		R/W
0003С9н	Memory Patch function - Patch address 5 high	PFAH5		R/W
0003САн	Memory Patch function - Patch address 6 low	PFAL6		R/W
0003СВн	Memory Patch function - Patch address 6 middle	PFAM6		R/W
0003ССн	Memory Patch function - Patch address 6 high	PFAH6		R/W
0003СDн	Memory Patch function - Patch address 7 low	PFAL7		R/W
0003СЕн	Memory Patch function - Patch address 7 middle	PFAM7		R/W
0003СFн	Memory Patch function - Patch address 7 high	PFAH7		R/W
0003D0н	Memory Patch function - Patch data 0 Low	PFDL0	PFD0	R/W
0003D1н	Memory Patch function - Patch data 0 High	PFDH0		R/W
0003D2н	Memory Patch function - Patch data 1 Low	PFDL1	PFD1	R/W
0003D3н	Memory Patch function - Patch data 1 High	PFDH1		R/W
0003D4н	Memory Patch function - Patch data 2 Low	PFDL2	PFD2	R/W
0003D5н	Memory Patch function - Patch data 2 High	PFDH2		R/W
0003D6н	Memory Patch function - Patch data 3 Low	PFDL3	PFD3	R/W
0003D7н	Memory Patch function - Patch data 3 High	PFDH3		R/W
0003D8н	Memory Patch function - Patch data 4 Low	PFDL4	PFD4	R/W
0003D9н	Memory Patch function - Patch data 4 High	PFDH4		R/W
0003DАн	Memory Patch function - Patch data 5 Low	PFDL5	PFD5	R/W

Interrupt vector table MB96(F)35x (3 of 3)

Vector number	Offset in vector ta- ble	Vector name	Cleared by DMA	Index in ICR to pro- gram	Description
67	2F0н				Reserved
68	2ЕСн	ICU9	Yes	68	Input Capture Unit 9
69	2Е8н	ICU10	Yes	69	Input Capture Unit 10
70	2Е4н				Reserved
71	2Е0н	OCU4	Yes	71	Output Compare Unit 4
72	2DC _H	OCU5	Yes	72	Output Compare Unit 5
73	2D8н	OCU6	Yes	73	Output Compare Unit 6
74	2D4н	OCU7	Yes	74	Output Compare Unit 7
75	2D0н				Reserved
76	2ССн				Reserved
77	2С8н	FRT0	Yes	77	Free Running Timer 0
78	2С4н	FRT1	Yes	78	Free Running Timer 1
79	2С0н	FRT2	Yes	79	Free Running Timer 2
80	2ВСн	FRT3	Yes	80	Free Running Timer 3
81	2В8н	RTC0	No	81	Real Timer Clock
82	2В4н	CAL0	No	82	Clock Calibration Unit
83	2В0н	IIC0	Yes	83	I2C interface
84	2АСн	ADC0	Yes	84	A/D Converter
85	2А8н	LINR2	Yes	85	LIN USART 2 RX
86	2А4н	LINT2	Yes	86	LIN USART 2 TX
87	2А0н	LINR3	Yes	87	LIN USART 3 RX
88	29Сн	LINT3	Yes	88	LIN USART 3 TX
89	298н	LINR7	Yes	89	LIN USART 7 RX
90	294н	LINT7	Yes	90	LIN USART 7 TX
91	290н	LINR8	Yes	91	LIN USART 8 RX
92	28Сн	LINT8	Yes	92	LIN USART 8 TX
93	288н	FLASH_A	No	93	Flash memory A (only Flash devices)

 $(T_A = -40$ °C to 125°C, $V_{CC} = AV_{CC} = 3.0V$ to 5.5V, $V_{SS} = AV_{SS} = 0V)$

Danamatan	Councile of	On dition (at T)		Value		- Remarks		
Parameter	Symbol	Condition (at T _A)	Тур	Max	Unit			
		Main Run mode with CLKS1/2 = CLKB =	+25°C	4	5	m A	MB96F353/F355	
		CLKS1/2 = CLKB = CLKP1/2 = 4MHz	+125°C	4.7	8	mA	WID90F353/F355	
	ICCMAIN	1 Flash/ROM wait state	+25°C	4.2	5.2			
		(CLKPLL, CLKSC and CLKRC stopped)	+125°C	4.9	8.2	mA	MB96F356	
		RC Run mode with CLKS1/2 = CLKB =	+25°C	2.5	3.5	mA	MB96F353/F355	
		CLK91/2 = CLKB = CLKP1/2 = 2MHz	+125°C	3.2	6.5	IIIA	WID90F333/F333	
	Iccrch	1 Flash/ROM wait state	+25°C	2.7	3.7		MPOOFOE	
		(CLKMC, CLKPLL and CLKSC stopped)	+125°C	3.4	6.7	mA	MB96F356	
	Iccrcl	RC Run mode with CLKS1/2 = CLKB =	+25°C	0.18	0.3	^	MPOCEOFO/FOFF	
		CLKP1/2 = 100kHz, SMCR:LPMS = 0	+125°C	0.73	3.1	mA	MB96F353/F355	
		1 Flash/ROM wait state	+25°C	0.4	0.6			
Power supply cur- rent in Run modes*		(CLKMC, CLKPLL and CLKSC stopped. Voltage regulator in high power mode)	+125°C	0.95	3.4	mA	MB96F356	
		RC Run mode with CLKS1/2 = CLKB =	+25°C	0.15	0.25			
		CLKP1/2 = 100kHz, SMCR:LPMS = 1 1 Flash/ROM wait state (CLKMC, CLKPLL and CLKSC stopped. Voltage regulator in low power mode, no Flash program- ming/erasing allowed)	+125°C	0.7	3.05	mA	MB96F353/F355/ F356	
		Sub Run mode with	+25°C	0.1	0.2			
		CLKS1/2 = CLKB = CLKP1/2 = 32kHz				-		
	Іссѕив	1 Flash/ROM wait state				mA	MB96F353/F355/	
	.55505	(CLKMC, CLKPLL and CLKRC stopped, no Flash programming/erasing al- lowed)	+125°C	0.65	3		F356	

 $(T_A = -40$ °C to 125°C, $V_{CC} = AV_{CC} = 3.0V$ to 5.5V, $V_{SS} = AV_{SS} = 0V)$

Barranatan	0	O 1'' (-1 T)		Value		D		
Parameter	Symbol	Condition (at T _A)	(at IA)		Max	Unit	Remarks	
		RC Sleep mode with CLKS1/2 = CLKP1/2 =	+25°C	0.08	0.2	mA	MB96F353/F355	
		100kHz, SMCR:LPMSS = 0	+125°C	0.59	2.95	1117	100000000000000000000000000000000000000	
		(CLKMC, CLKPLL and CLKSC stopped. Voltage	+25°C	0.3	0.5		MDOCESEC	
	Iccsrcl	regulator in high power mode)	+125°C	0.8	3.3	mA	MB96F356	
Power supply cur-	TOOSINGE	RC Sleep mode with CLKS1/2 = CLKP1/2 =	+25°C	0.05	0.15			
rent in Sleep modes*		100kHz, SMCR:LPMSS = 1 (CLKMC, CLKPLL and CLKSC stopped. Voltage regulator in low power mode)	+125°C	0.56	2.9	mA	MB96F353/F355/ F356	
	Іссѕѕив	Sub Sleep mode with CLKS1/2 = CLKP1/2 =	+25°C	0.04	0.12			
		32kHz (CLKMC, CLKPLL and CLKRC stopped)	+125°C	0.54	2.9	mA	MB96F353/F355/ F356	
	Ісстріі	PLL Timer mode with CLKMC = 4MHz, CLKPLL = 48MHz (CLKRC and CLKSC stopped)	+25°C	1.3	1.8	mA	MB96F353/F355	
			+125°C	1.9	4.8	1117	1010001 000/1 000	
			+25°C	1.5	2	mA	MB96F356	
		,	+125°C	2.1	5			
		Main Timer mode with CLKMC = 4MHz,	+25°C	0.11	0.2	mA	MB96F353/F355	
Power supply cur- rent in Timer		SMCR:LPMSS = 0 (CLKPLL, CLKRC and	+125°C	0.63	3			
modes*		CLKSC stopped. Voltage regulator in high power	+25°C	0.35	0.5	mA	MB96F356	
	I CCTMAIN	mode)	+125°C	0.85	3.3			
		Main Timer mode with CLKMC = 4MHz, SMCR:LPMSS = 1	+25°C	0.08	0.15			
		(CLKPLL, CLKRC and CLKSC stopped. Voltage regulator in low power mode)	+125°C	0.6	2.9	mA	MB96F353/F355/ F356	

4. AC Characteristics

Source Clock timing

 $(T_A = -40^{\circ}C \text{ to } 125^{\circ}C, V_{CC} = AV_{CC} = 3.0V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V)$

Doromotor	Cumbal	Pin		Value		Unit	Remarks		
Parameter	Symbol	Pin	Min	Тур	Max	Unit	Remarks		
			3	-	16	MHz	When using a crystal oscillator, PLL off		
Clock frequency	fc	X0, X1	0	-	16	MHz	When using an opposite phase external clock, PLL off		
			3.5	-	16	MHz	When using a crystal oscillator or opposite phase external clock, PLL on		
Clock frequency	f FCI	X0	0	-	56	MHz	When using a single phase external clock in "Fast Clock Input mode", PLL off		
Clock frequency	IFCI	λ0	3.5	-	56	MHz	When using a single phase external clock in "Fast Clock Input mode", PLL on		
			32	32.768	100	kHz	When using an oscillation circuit		
Clock frequency	fcL	X0A, X1A	0	-	100	kHz	When using an opposite phase external clock		
		X0A	0	-	50	kHz	When using a single phase external clock		
Clock frequency	t.		50	100	200	kHz	When using slow frequency of RC oscillator		
Clock frequency	fcr	-	1	2	4	MHz	When using fast frequency of RC oscillator		
RC clock stabilization time	trcstab	-	64 or	256 RC c	clock cyc	cles	Applied after any reset and when activating the RC oscillator. MB96F356: 64 cycles others: 256 cycles		
PLL Clock fre- quency	f cLKVCO	-	64	-	200	MHz	Permitted VCO output frequency of PLL (CLKVCO)		
PLL Phase Jitter	Tpskew	-	-	-	± 5 ns		For CLKMC (PLL input clock) ≥ 4MHz, jitter coming from external oscillator, crystal or resonator is not covered		
Input clock pulse width	Pwh, Pwl	X0,X1	8	-	-	ns	Duty ratio is about 30% to 70%		
Input clock pulse width	Pwhl, Pwll	X0A,X1A	5	-	-	μs			

External Bus timing

Note: The values given below are for an I/O driving strength IO_{drive} = 5mA. If IO_{drive} is 2mA, all the maximum output timing described in the different tables must then be increased by 10ns.

Basic Timing

(T_A = -40 °C to +125 °C, Vcc = 5.0 V \pm 10%, Vss = 0.0 V, IO_{drive} = 5mA, C_L = 50pF)

Parameter	Symbol	Pin	Condition	Val	lue	Unit	Remarks
Parameter	Symbol	PIII	Condition	Min	Max	Ullit	
	t cyc			25	_		
ECLK	t chcL	ECLK		tcyc/2-5	tcyc/2+5	ns	
	t clch			tcyc/2-5	tcyc/2+5		
	t снсвн			-20	20		
ECLK o	t CHCBL	CSn, UBX,		-20	20	nc	
UBX/ LBX / CSn time	tсьсвн	LBX, ECLK		-20	20	- ns	
	t clcbl			-20	20		
	t chlh	ALE, ECLK	_	-10	10	- ns	
ECLK o ALE time	t CHLL			-10	10		
EOLN → ALE IIIIe	t CLLH			-10	10		
	tclll			-10	10		
	t CHAV	A[23:16],	_	-15	15	- ns	
ECLK → address valid time	tclav	ECLK		-15	15		
	t CLADV	AD[15:0],		-15	15	- ns	
	t CHADV	ECLK		-15	15		
	t chrwh			-10	10		
$ECLK \to RDX / WRX$ time	t CHRWL	RDX, WRX, WRLX,WRHX,		-10	10	nc	
	t clrwh	ECLK		-10	10	ns	
	tclrwl			-10	10		

(TA = -40 °C to +125 °C, Vcc = 3.0 to 4.5V, Vss = 0.0 V, IOdrive = 5mA, CL = 50pF)

Donomotor	Sym-	D:-	Conditions	Va	l loc!4		
Parameter	bol	Pin	Conditions	Min	Max	Unit	Remarks
	t avrl	RDX, A[23:16]	EACL:ACE=0	3tcyc/2 – 20	_	ns	
Valid address ⇒ RDX ↓ time	LAVRL	KDX, A[23.10]	EACL:ACE=1	5tcyc/2 - 20	_	115	
⇒ KDX ↓ time	t advrl	RDX, AD[15:0]	EACL:ACE=0	tcyc - 20	_	ns	
			EACL:ACE=1	2tcyc - 20	_		
	tavdv	A[23:16], AD[15:0]	EACL:ACE=0	_	3tcyc - 60	ns	w/o cycle extension
Valid address ⇒ Valid data input	LAVDV		EACL:ACE=1	_	4tcyc - 60	115	
	t advdv	AD[15:0]	EACL:ACE=0	_	5tcyc/2 - 60	ne	w/o cycle extension
			EACL:ACE=1	_	7tcyc/2 - 60	ns	
RDX pulse width	t rlrh	RDX	_	3tcyc/2 - 8	_	ns	w/o cycle extension
$RDX \downarrow \Rightarrow Valid \ data \ input$	t RLDV	RDX, AD[15:0]	_		3tcyc/2 - 55	ns	w/o cycle extension
$RDX \uparrow \Rightarrow Data hold time$	t RHDX	RDX, AD[15:0]	_	0		ns	
Address valid \Rightarrow Data hold time	t AXDX	A[23:16]	_	0	_	ns	
$RDX \uparrow \Rightarrow ALE \uparrow time$	tкнгн	RDX, ALE	EACL:STS=1 and EACL:ACE=1	3tcyc/2 – 15	_	ne	
			other ECL:STS, EACL:ACE setting	tcyc/2 - 15	_	ns	
Valid address	t avch	A[23:16], ECLK		tcyc - 20	_	nc	
⇒ ECLK ↑ time	tadvch	AD[15:0], ECLK		tcyc/2 - 20		ns	
$RDX \downarrow \Rightarrow ECLK \uparrow time$	t RLCH	RDX, ECLK		tcyc/2 - 15		ns	
$ALE \downarrow \Rightarrow RDX \downarrow time$	t llrl	ALE, RDX	EACL:STS=0	tcyc/2 - 15		ns	
	LLLKL	ALL, NOA	EACL:STS=1	- 15 —		113	
ECLK [↑] ⇒ Valid data input	t CHDV	AD[15:0], ECLK	_	_	tcyc - 55	ns	

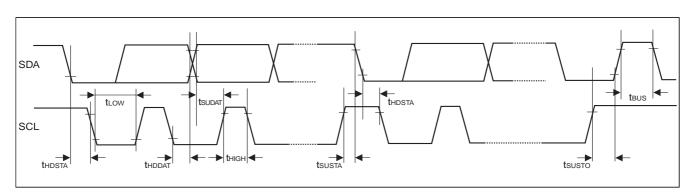
I²C Timing

 $(T_A = -40^{\circ}C \text{ to } 125^{\circ}C, V_{CC} = AV_{CC} = 3.0V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V)$

Paramatar	Cumab al	Standard-mode		Fast-mode*1		Unit
Parameter	Symbol	Min	Max	Min	Max	Unit
SCL clock frequency	fscL	0	100	0	400	kHz
Hold time (repeated) START condition SDA↓→SCL↓	t HDSTA	4.0		0.6	_	μs
"L" width of the SCL clock	t LOW	4.7		1.3	_	μs
"H" width of the SCL clock	t HIGH	4.0		0.6	_	μs
Set-up time for a repeated START condition SCL $\uparrow \rightarrow$ SDA \downarrow	t susta	4.7		0.6	_	μs
Data hold time SCL↓→SDA↓↑	t hddat	0	3.45	0	0.9	μs
Data set-up time SDA↓↑→SCL↑	t sudat	250		100	_	ns
Set-up time for STOP condition SCL↑→SDA↑	t susto	4.0		0.6	_	μs
Bus free time between a STOP and START condition	t BUS	4.7	_	1.3	_	μs
Output fall time from 0.7*Vcc to 0.3*Vcc with a bus capacitance from 10 pF to 400 pF	t of	20 + 0.1*C _b *2	250	20 + 0.1*C _b * ²	250	ns
Capacitive load for each bus line	Сь	_	400	_	400	pF
Pulse width of spikes which will be sup- pressed by input noise filter	t sp	n/a	n/a	0	1*tclkp1*3	ns

^{*1 :} For use at over 100 kHz, set the peripheral clock 1 to at least 6 MHz.

^{*3:} tclkP1 is the cycle time of the periperal clock CLKP1.



- Voн = 0.7 * Vcc
- VoL = 0.3 * Vcc
- CMOS Hysteresis 0.7/0.3 input selected

^{*2 :} C_b = capacitance of one bus line in pF.

Definition of A/D Converter Terms

Resolution: Analog variation that is recognized by an A/D converter.

<u>Total error</u>: Difference between the actual value and the ideal value. The total error includes zero transition error, full-scale transition error and nonlinearity error.

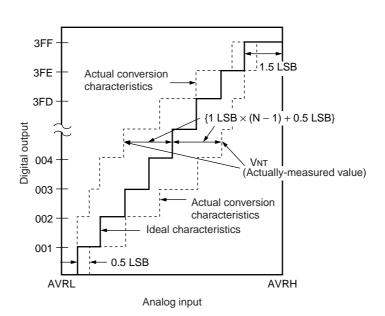
Nonlinearity error: Deviation between a line across zero-transition line ("00 0000 0000" <--> "00 0000 0001") and full-scale transition line ("11 1111 1110" <--> "11 1111 1111") and actual conversion characteristics.

<u>Differential nonlinearity error:</u> Deviation of input voltage, which is required for changing output code by 1 LSB, from an ideal value.

Zero reading voltage: Input voltage which results in the minimum conversion value.

Full scale reading voltage: Input voltage which results in the maximum conversion value.

Total error



Total error of digital output "N" =
$$\frac{V_{NT} - \{1 \text{ LSB} \times (N-1) + 0.5 \text{ LSB}\}}{1 \text{ LSB}} \text{ [LSB]}$$

$$1 \text{ LSB} = \text{ (Ideal value)} \frac{AVRH - AVRL}{1024} \text{ [V]}$$

N: A/D converter digital output value

Vot (Ideal value) = AVRL + 0.5 LSB [V]

VFST (Ideal value) = AVRH - 1.5 LSB [V]

 V_{NT} : A voltage at which digital output transitions from (N-1) to N.

7. FLASH memory program/erase characteristics

 $(T_A = -40^{\circ}C \text{ to } 105^{\circ}C, V_{CC} = AV_{CC} = 3.0V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V)$

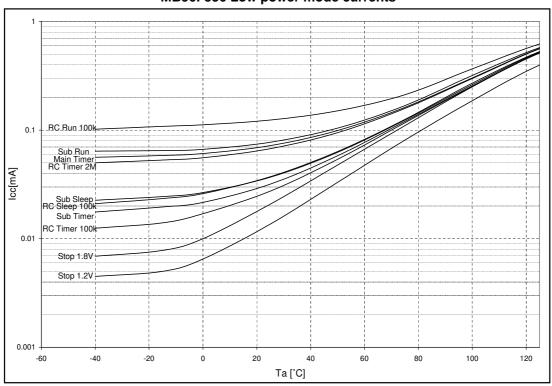
Parameter	Value			Unit	Remarks	
Faranietei	Min	Тур	Max	Oilit	Remarks	
Sector erase time	-	0.9	3.6	S	Without erasure pre-program- ming time	
Chip erase time	-	n*0.9	n*3.6	S	Without erasure pre-program- ming time (n is the number of Flash sector of the device)	
Word (16-bit width) programming time	-	23	370	us	Without overhead time for sub- mitting write command	
Program/Erase cycle	10 000	-	-	cycle		
Flash data retention time	20	-	-	year	*1	

^{*1:} This value was converted from the results of evaluating the reliability of the technology (using Arrhenius equation to convert high temperature measurements into normalized value at 85°C)

Mode name	Details
RC Run 2M	RC Run mode current I _{CCRCH} with the following settings: RC oscillator set to 2MHz (CKFCR:RCFS = 1) f _{CLKS1} = f _{CLKS2} = f _{CLKB} = f _{CLKP1} = f _{CLKP2} = 2MHz Regulator in High Power Mode Core voltage at 1.8V (VRCR:HPM[1:0] = 10 _B) 1 Flash/ROM wait states (MTCRA=0239 _H) PLL, Main oscillator and Sub oscillator stopped
RC Run 100k	RC Run mode current I _{CCRCL} with the following settings: RC oscillator set to 100kHz (CKFCR:RCFS = 0) f _{CLKS1} = f _{CLKS2} = f _{CLKB} = f _{CLKP1} = f _{CLKP2} = 100kHz Regulator in Low Power Mode A (SMCR:LPMS = 1) Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) 1 Flash/ROM wait states (MTCRA=0239 _H) PLL, Main oscillator and Sub oscillator stopped
Sub Run	Sub Run mode current I _{CCSUB} with the following settings: • f _{CLKS1} = f _{CLKS2} = f _{CLKB} = f _{CLKP1} = f _{CLKP2} = 32kHz • Regulator in Low Power Mode A (by hardware) • Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) • 1 Flash/ROM wait states (MTCRA=0239 _H) • PLL, RC oscillator and Main oscillator stopped
PLL Sleep 56	 PLL Sleep mode current I_{CCSPLL} with the following settings: f_{CLKS1} = f_{CLKS2} = f_{CLKP1} = 56MHz f_{CLKP2} = 28MHz Regulator in High Power Mode Core voltage at 1.9V (VRCR:HPM[1:0] = 11_B) RC oscillator and Sub oscillator stopped
PLL Sleep 48	PLL Sleep mode current I _{CCSPLL} with the following settings: • f _{CLKS1} = f _{CLKS2} = 96MHz • f _{CLKP1} = 48MHz • f _{CLKP2} = 24MHz • Regulator in High Power Mode • Core voltage at 1.9V (VRCR:HPM[1:0] = 11 _B) • RC oscillator and Sub oscillator stopped
PLL Sleep 24	PLL Sleep mode current I _{CCSPLL} with the following settings: • f _{CLKS1} = f _{CLKS2} = 48MHz • f _{CLKP1} = f _{CLKP2} = 24MHz • Regulator in High Power Mode • Core voltage at 1.8V (VRCR:HPM[1:0] = 10 _B) • RC oscillator and Sub oscillator stopped
Main Sleep	Main Sleep mode current I _{CCSMAIN} with the following settings: • f _{CLKS1} = f _{CLKS2} = f _{CLKP1} = f _{CLKP2} = 4MHz • Regulator in High Power Mode • Core voltage at 1.8V (VRCR:HPM[1:0] = 10 _B) • PLL, RC oscillator and Sub oscillator stopped

Mode name	Details
RC Sleep 2M	RC Sleep mode current I _{CCSRCH} with the following settings: RC oscillator set to 2MHz (CKFCR:RCFS = 1) f _{CLKS1} = f _{CLKS2} = f _{CLKP1} = f _{CLKP2} = 2MHz Regulator in High Power Mode Core voltage at 1.8V (VRCR:HPM[1:0] = 10 _B) PLL, Main oscillator and Sub oscillator stopped
RC Sleep 100k	RC Sleep mode current I _{CCSRCL} with the following settings: RC oscillator set to 100kHz (CKFCR:RCFS = 0) f _{CLKS1} = f _{CLKS2} = f _{CLKP1} = f _{CLKP2} = 100kHz Regulator in Low Power Mode A (SMCR:LPMSS = 1) Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) PLL, Main oscillator and Sub oscillator stopped
Sub Sleep	Sub Sleep mode current I _{CCSSUB} with the following settings: • f _{CLKS1} = f _{CLKS2} = f _{CLKP1} = f _{CLKP2} = 32kHz • Regulator in Low Power Mode A (by hardware) • Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) • PLL, RC oscillator and Main oscillator stopped
PLL Timer 48	PLL Timer mode current I _{CCTPLL} with the following settings: • f _{CLKS1} = f _{CLKS2} = 48MHz • Regulator in High Power Mode • Core voltage at 1.8V (VRCR:HPM[1:0] = 10 _B) • RC oscillator and Sub oscillator stopped
Main Timer	Main Timer mode current I _{CCTMAIN} with the following settings: • f _{CLKS1} = f _{CLKS2} = 4MHz • Regulator in Low Power Mode A (SMCR:LPMSS = 1) • Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) • PLL, RC oscillator and Sub oscillator stopped
RC Timer 2M	RC Timer mode current I _{CCTRCH} with the following settings: RC oscillator set to 2MHz (CKFCR:RCFS = 1) f _{CLKS1} = f _{CLKS2} = 2MHz Regulator in Low Power Mode A (SMCR:LPMSS = 1) Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) PLL, Main oscillator and Sub oscillator stopped
RC Timer 100k	RC Timer mode current I _{CCTRCL} with the following settings: RC oscillator set to 100kHz (CKFCR:RCFS = 0) f _{CLKS1} = f _{CLKS2} = 100kHz Regulator in Low Power Mode A (SMCR:LPMSS = 1) Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) PLL, Main oscillator and Sub oscillator stopped
Sub Timer	Sub Timer mode current I _{CCTSUB} with the following settings: • f _{CLKS1} = f _{CLKS2} = 32kHz • Regulator in Low Power Mode A (by hardware) • Core voltage at 1.8V (VRCR:LPMA[2:0] = 110 _B) • PLL, RC oscillator and Main oscillator stopped

MB96F356 Low power mode currents



MCU without CAN controller

Part number	Flash/ROM	Subclock	Persistent Low Volt- age Reset	Package
MB96F353ASB PMC-GSE2		No	No -	64 pins Plastic LQFP (FPT-64P-M23)
MB96F353AWB PMC-GSE2	Flach A (O6KP)	Yes		
MB96F353ASB PMC1-GSE2	Flash A (96KB)	No		64 pins Plastic LQFP
MB96F353AWB PMC1-GSE2		Yes		(FPT-64P-M24)
MB96F355ASB PMC-GSE2		No		64 pins Plastic LQFP
MB96F355AWB PMC-GSE2	Floob A (460KB)	Yes		(FPT-64P-M23)
MB96F355ASB PMC1-GSE2	Flash A (160KB)	No		64 pins Plastic LQFP
MB96F355AWB PMC1-GSE2		Yes		(FPT-64P-M24)
MB96F356ASB PMC-GSE2		No		64 pins Plastic LQFP
MB96F356AWB PMC-GSE2		Yes		(FPT-64P-M23)
MB96F356ASB PMC1-GSE2	Flash A (288KB)	No		64 pins Plastic LQFP
MB96F356AWB PMC1-GSE2		Yes		(FPT-64P-M24)

This datasheet is also valid for the following outdated devices:

MB96F356YSA, MB96F356RSA, MB96F356YWA, MB96F356RWA, MB96F356ASA, MB96F356AWA, MB96F353RSA, MB96F353RWA, MB96F355RSA, MB96F355ASA, MB96F355ASA, MB96F355AWA, MB96F355ASA, MB96F355AWA.

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